

Silicon NPN Epitaxial Planar Type

MT6L54E

VHF-UHF Band Low Noise Amplifier Application

VHF-UHF Band Oscillator Application

Unit in mm

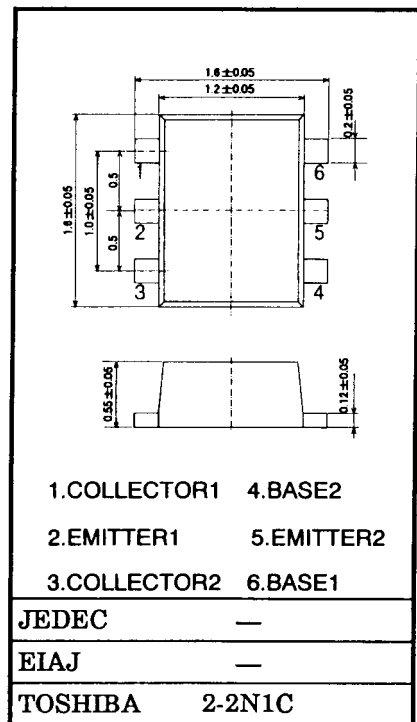
- Two devices are built in to the super-thin and ultra super mini (6 pin) package: ES6

	Q1: SSM (TESM)	Q2: TESM
Three pin (SSM/TESM) type part No.	MT3S06S (MT3S06T)	MT3S08T

Maximum Ratings (Ta = 25°C)

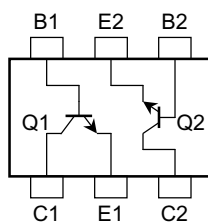
Characteristics	Symbol	Q1	Q2	Unit
Collector-base voltage	V_{CBO}	10	20	V
Collector-emitter voltage	V_{CEO}	5	8	V
Emitter-base voltage	V_{EBO}	1.5	1.5	V
Collector current	I_C	15	40	mA
Base current	I_B	7	10	mA
Collector power dissipation	P_C (Note 1)	100		mW
Junction temperature	T_j	125		°C
Storage temperature range	T_{stg}	-55~125		°C

Note 1: Total power dissipation of Q1 and Q2

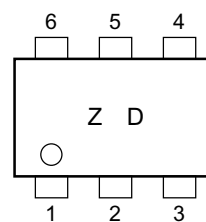


Weight: 0.003 g

Assignment



MarkingPin



000707EAA1

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

Electrical Characteristics Q1-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	70	—	140	—
Transition frequency	f_T	$V_{CE} = 3\text{ V}, I_C = 5\text{ mA}$	7	10	—	GHz
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 2\text{ GHz}$	—	7.5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 3\text{ V}, I_C = 7\text{ mA}, f = 2\text{ GHz}$	4.5	8	—	
Noise figure	NF (1)	$V_{CE} = 1\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$	—	1.7	3	dB
	NF (2)	$V_{CE} = 3\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz}$	—	1.6	3	
Reverse transfer capacitance	C_{re}	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	0.35	0.75	pF

Electrical Characteristics Q2-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 10\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	80	—	140	—
Transition frequency	f_T	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	2	4.5	—	GHz
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	—	9.5	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 3\text{ V}, I_C = 20\text{ mA}, f = 1\text{ GHz}$	9.5	12.5	—	
Noise figure	NF	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	—	1.4	2.5	dB
Reverse transfer capacitance	C_{re}	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	0.55	0.95	pF

Caution

This device electrostatic sensitivity. Please handle with caution.